



SILICON HIGH SPEED POWER TRANSISTOR

2SC 2525 2SC 2526

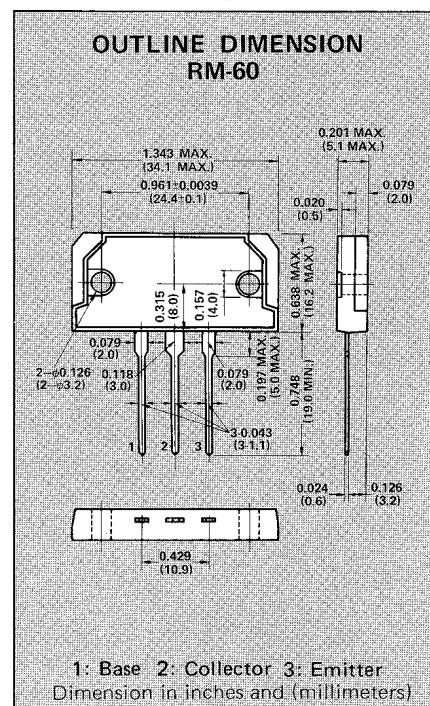
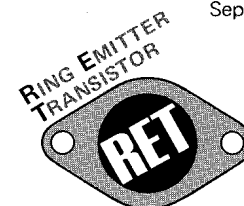
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SILICON NPN RING EMITTER TRANSISTOR (RET)

The 2SC 2525/2SC 2526 are silicon NPN general purpose, high power switching transistors fabricated with Fujitsu's unique Ring Emitter Transistor (RET) technology. RET devices are constructed with multiple emitters connected through diffused ballast resistors which provide uniform current density. This structure permits the design of high power transistors with exceptional switching characteristics and frequency response in high current applications.

The 2SC 2525/2SC 2526 are especially well-suited for High frequency power amplifiers, Audio power amplifiers, Switching regulators and DC-DC Converters. PNP complements, 2SA 1075/2SA 1076, are available.

- High $f_T = 80$ MHz (typ)
- Ultra fast switching speed
- Excellent Safe Operating Area
- Improved reverse Second-Breakdown Capability



ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		2SC 2525	2SC 2526	
Collector to Base Voltage	V_{CBO}	120	160	V
Emitter to Base Voltage	V_{EBO}	7	7	V
Collector to Emitter Voltage	V_{CEO}	120	160	V
Collector Current	I_C	12	12	A
Collector Power Dissipation ($T_C = 25^\circ\text{C}$)	P_C	120	120	W
Junction Temperature	T_j	+150		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 ~ +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Limits						Unit
			2SC 2525			2SC 2526			
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120V/160V, I_E = 0$	—	—	50/—	—	—	—/50	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7V, I_C = 0$	—	—	50	—	—	50	μA
Collector Cutoff Current	I_{CEO}	$V_{CE} = 120V/160V, R_{BE} = \infty$	—	—	1/—			—/1	mA
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu A, I_E = 0$	120	—	—	160	—	—	V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu A, I_C = 0$	7	—	—	7	—	—	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	120	—	—	160	—	—	V
DC Current Gain	h_{FE1}	$V_{CE} = 5V, I_C = 1A$ *	60	—	200	60	—	200	
DC Current Gain	h_{FE2}	$V_{CE} = 5V, I_C = 7A$ *	40	—	—	40	—	—	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 0.5A$ *	—	0.7	1.8	—	0.7	1.8	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 5A$ *	—	1.25	1.7	—	1.25	1.7	V
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 1A, f = 10MHz$	50	80	—	50	80	—	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	180	300	—	180	300	pF
Rise Time	t_r	$I_C = 7.5A, R_L = 4\Omega$ $I_{B1} = -I_{B2} = 0.75A$	—	0.3	—	—	0.3	—	μs
Storage Time	t_{stg}		—	1.3	—	—	1.3	—	μs
Fall Time	t_f		—	0.2	—	—	0.2	—	μs

* Pulsed: Pulse Width $\leq 300\mu\text{s}$
Duty Cycle $\leq 6\%$